

# MOSFET

Metal Oxide Semiconductor Field Effect Transistor

## CoolMOS C6

600V CoolMOS™ C6 Power Transistor  
IPx60R125C6

## Data Sheet

Rev. 2.1, 2010-02-09  
Final

Industrial & Multimarket

## 600V CoolMOS™ C6 Power Transistor

IPA60R125C6, IPB60R125C6  
IPP60R125C6 IPW60R125C6

### 1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ C6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The offered devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter, and cooler.

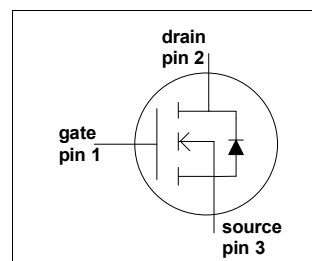
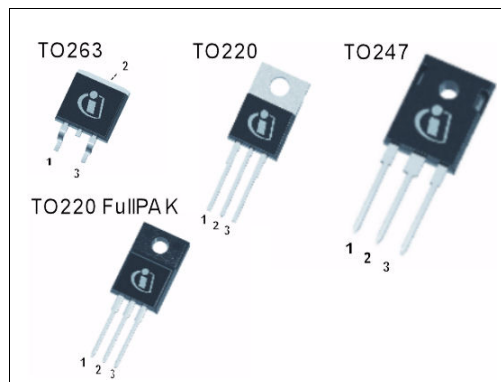
#### Features

- Extremely low losses due to very low FOM  $R_{DS(on)} \cdot Q_g$  and  $E_{oss}$
- Very high commutation ruggedness
- Easy to use/drive
- JEDEC<sup>1)</sup> qualified, Pb-free plating, Halogen free

#### Applications

PFC stages, hard switching PWM stages and resonant switching PWM stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom, UPS and Solar.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.



**Table 1 Key Performance Parameters**

| Parameter            | Value | Unit       |
|----------------------|-------|------------|
| $V_{DS} @ T_{j,max}$ | 650   | V          |
| $R_{DS(on),max}$     | 0.125 | $\Omega$   |
| $Q_{g,typ}$          | 96    | nC         |
| $I_{D,pulse}$        | 89    | A          |
| $E_{oss} @ 400V$     | 7.6   | $\mu J$    |
| Body diode $di/dt$   | 500   | A/ $\mu s$ |

| Type / Ordering Code | Package          | Marking | Related Links                                                                                                                                       |
|----------------------|------------------|---------|-----------------------------------------------------------------------------------------------------------------------------------------------------|
| IPW60R125C6          | PG-TO247         | 6R125C6 | <a href="#">IFX C6 Product Brief</a><br><a href="#">IFX C6 Portfolio</a><br><a href="#">IFX CoolMOS Webpage</a><br><a href="#">IFX Design tools</a> |
| IPB60R125C6          | PG-TO263         |         |                                                                                                                                                     |
| IPP60R125C6          | PG-TO220         |         |                                                                                                                                                     |
| IPA60R125C6          | PG-TO220 FullPAK |         |                                                                                                                                                     |

1) J-STD20 and JESD22

## Table of Contents

|   |                                           |    |
|---|-------------------------------------------|----|
| 1 | Description .....                         | 2  |
|   | Table of Contents .....                   | 3  |
| 2 | Maximum ratings .....                     | 4  |
| 3 | Thermal characteristics .....             | 5  |
| 4 | Electrical characteristics .....          | 6  |
| 5 | Electrical characteristics diagrams ..... | 8  |
| 6 | Test circuits .....                       | 13 |
| 7 | Package outlines .....                    | 14 |
| 8 | Revision History .....                    | 18 |

## 2 Maximum ratings

at  $T_j = 25\text{ °C}$ , unless otherwise specified.

**Table 2 Maximum ratings**

| Parameter                                     | Symbol         | Values |      |      | Unit | Note / Test Condition                                                     |
|-----------------------------------------------|----------------|--------|------|------|------|---------------------------------------------------------------------------|
|                                               |                | Min.   | Typ. | Max. |      |                                                                           |
| Continuous drain current <sup>1)</sup>        | $I_D$          | -      | -    | 30   | A    | $T_C = 25\text{ °C}$                                                      |
|                                               |                |        |      | 19   |      | $T_C = 100\text{ °C}$                                                     |
| Pulsed drain current <sup>2)</sup>            | $I_{D,pulse}$  | -      | -    | 89   | A    | $T_C = 25\text{ °C}$                                                      |
| Avalanche energy, single pulse                | $E_{AS}$       | -      | -    | 636  | mJ   | $I_D = 5.2\text{ A}, V_{DD} = 50\text{ V}$<br>(see table 21)              |
| Avalanche energy, repetitive                  | $E_{AR}$       | -      | -    | 0.96 |      | $I_D = 5.2\text{ A}, V_{DD} = 50\text{ V}$                                |
| Avalanche current, repetitive                 | $I_{AR}$       | -      | -    | 5.2  | A    |                                                                           |
| MOSFET dv/dt ruggedness                       | dv/dt          | -      | -    | 50   | V/ns | $V_{DS} = 0 \dots 480\text{ V}$                                           |
| Gate source voltage                           | $V_{GS}$       | -20    | -    | 20   | V    | static                                                                    |
|                                               |                | -30    |      | 30   |      | AC ( $f > 1\text{ Hz}$ )                                                  |
| Power dissipation for TO-220, TO-247, TO-263  | $P_{tot}$      | -      | -    | 219  | W    | $T_C = 25\text{ °C}$                                                      |
| Power dissipation for TO-220 FullPAK          | $P_{tot}$      | -      | -    | 34   |      |                                                                           |
| Operating and storage temperature             | $T_j, T_{stg}$ | -55    | -    | 150  | °C   |                                                                           |
| Mounting torque TO-220, TO-247                |                | -      | -    | 60   | Ncm  | M3 and M3.5 screws                                                        |
| Mounting torque TO-220 FullPAK                |                |        |      | 50   |      | M2.5 screws                                                               |
| Continuous diode forward current              | $I_S$          | -      | -    | 26   | A    | $T_C = 25\text{ °C}$                                                      |
| Diode pulse current <sup>2)</sup>             | $I_{S,pulse}$  | -      | -    | 89   | A    | $T_C = 25\text{ °C}$                                                      |
| Reverse diode dv/dt <sup>3)</sup>             | dv/dt          | -      | -    | 15   | V/ns | $V_{DS} = 0 \dots 400\text{ V}, I_{SD} \leq I_D,$<br>$T_j = 25\text{ °C}$ |
| Maximum diode commutation speed <sup>3)</sup> | di/dt          |        |      | 500  | A/μs | (see table 22)                                                            |

1) Limited by  $T_{j,max}$ . Maximum duty cycle  $D = 0.75$

2) Pulse width  $t_p$  limited by  $T_{j,max}$

3) Identical low side and high side switch with identical  $R_G$

### 3 Thermal characteristics

**Table 3 Thermal characteristics TO-220 (IPP60R125C6), TO-247 (IPW60R125C6)**

| Parameter                                                  | Symbol     | Values |      |      | Unit | Note / Test Condition                 |
|------------------------------------------------------------|------------|--------|------|------|------|---------------------------------------|
|                                                            |            | Min.   | Typ. | Max. |      |                                       |
| Thermal resistance, junction - case                        | $R_{thJC}$ | -      | -    | 0.57 | °C/W | leaded                                |
| Thermal resistance, junction - ambient                     | $R_{thJA}$ | -      | -    | 62   |      |                                       |
| Soldering temperature, wavesoldering only allowed at leads | $T_{sold}$ | -      | -    | 260  | °C   | 1.6 mm (0.063 in.) from case for 10 s |

**Table 4 Thermal characteristics TO-220FullPAK (IPA60R125C6)**

| Parameter                                                  | Symbol     | Values |      |      | Unit | Note / Test Condition                 |
|------------------------------------------------------------|------------|--------|------|------|------|---------------------------------------|
|                                                            |            | Min.   | Typ. | Max. |      |                                       |
| Thermal resistance, junction - case                        | $R_{thJC}$ | -      | -    | 3.65 | °C/W | leaded                                |
| Thermal resistance, junction - ambient                     | $R_{thJA}$ | -      | -    | 80   |      |                                       |
| Soldering temperature, wavesoldering only allowed at leads | $T_{sold}$ | -      | -    | 260  | °C   | 1.6 mm (0.063 in.) from case for 10 s |

**Table 5 Thermal characteristics TO-263 (IPB60R125C6)**

| Parameter                                               | Symbol     | Values |      |      | Unit | Note / Test Condition                         |
|---------------------------------------------------------|------------|--------|------|------|------|-----------------------------------------------|
|                                                         |            | Min.   | Typ. | Max. |      |                                               |
| Thermal resistance, junction - case                     | $R_{thJC}$ | -      | -    | 0.57 | °C/W | SMD version, device on PCB, minimal footprint |
| Thermal resistance, junction - ambient                  | $R_{thJA}$ | -      | -    | 62   |      |                                               |
|                                                         |            | -      | 35   | -    |      |                                               |
| Soldering temperature, wave- & reflow soldering allowed | $T_{sold}$ | -      | -    | 260  | °C   | reflow MSL1                                   |

1) Device on 40mm\*40mm\*1.5mm one layer epoxy PCB FR4 with 6cm<sup>2</sup> copper area (thickness 70µm) for drain connection. PCB is vertical without air stream cooling.

## 4 Electrical characteristics

Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified.

**Table 6 Static characteristics**

| Parameter                        | Symbol        | Values |      |       | Unit          | Note / Test Condition                                                |
|----------------------------------|---------------|--------|------|-------|---------------|----------------------------------------------------------------------|
|                                  |               | Min.   | Typ. | Max.  |               |                                                                      |
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | 600    | -    | -     | V             | $V_{GS}=0\text{ V}$ , $I_D=0.25\text{ mA}$                           |
| Gate threshold voltage           | $V_{GS(th)}$  | 2.5    | 3    | 3.5   |               | $V_{DS}=V_{GS}$ , $I_D=0.96\text{ mA}$                               |
| Zero gate voltage drain current  | $I_{DSS}$     | -      | -    | 2     | $\mu\text{A}$ | $V_{DS}=600\text{ V}$ , $V_{GS}=0\text{ V}$ ,<br>$T_j=25\text{ °C}$  |
|                                  |               | -      | 20   | -     |               | $V_{DS}=600\text{ V}$ , $V_{GS}=0\text{ V}$ ,<br>$T_j=150\text{ °C}$ |
| Gate-source leakage current      | $I_{GSS}$     | -      | -    | 100   | nA            | $V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$                           |
| Drain-source on-state resistance | $R_{DS(on)}$  | -      | 0.11 | 0.125 | $\Omega$      | $V_{GS}=10\text{ V}$ , $I_D=14.5\text{ A}$ ,<br>$T_j=25\text{ °C}$   |
|                                  |               | -      | 0.29 | -     |               | $V_{GS}=10\text{ V}$ , $I_D=14.5\text{ A}$ ,<br>$T_j=150\text{ °C}$  |
| Gate resistance                  | $R_G$         | -      | 3.7  | -     | $\Omega$      | $f=1\text{ MHz}$ , open drain                                        |

**Table 7 Dynamic characteristics**

| Parameter                                                  | Symbol       | Values |      |      | Unit | Note / Test Condition                                                                                        |
|------------------------------------------------------------|--------------|--------|------|------|------|--------------------------------------------------------------------------------------------------------------|
|                                                            |              | Min.   | Typ. | Max. |      |                                                                                                              |
| Input capacitance                                          | $C_{iss}$    | -      | 2127 | -    | pF   | $V_{GS}=0\text{ V}$ , $V_{DS}=100\text{ V}$ ,<br>$f=1\text{ MHz}$                                            |
| Output capacitance                                         | $C_{oss}$    | -      | 125  | -    |      |                                                                                                              |
| Effective output capacitance, energy related <sup>1)</sup> | $C_{o(er)}$  | -      | 82   | -    |      | $V_{GS}=0\text{ V}$ ,<br>$V_{DS}=0\dots480\text{ V}$                                                         |
| Effective output capacitance, time related <sup>2)</sup>   | $C_{o(tr)}$  | -      | 400  | -    |      | $I_D=\text{constant}$ , $V_{GS}=0\text{ V}$<br>$V_{DS}=0\dots480\text{ V}$                                   |
| Turn-on delay time                                         | $t_{d(on)}$  | -      | 15   | -    | ns   | $V_{DD}=400\text{ V}$ ,<br>$V_{GS}=13\text{ V}$ , $I_D=14.5\text{ A}$ ,<br>$R_G=1.7\Omega$<br>(see table 20) |
| Rise time                                                  | $t_r$        | -      | 12   | -    |      |                                                                                                              |
| Turn-off delay time                                        | $t_{d(off)}$ | -      | 83   | -    |      |                                                                                                              |
| Fall time                                                  | $t_f$        | -      | 7    | -    |      |                                                                                                              |

1)  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{(BR)DSS}$

2)  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{(BR)DSS}$

**Table 8 Gate charge characteristics**

| Parameter             | Symbol        | Values |      |      | Unit | Note / Test Condition                                                                |
|-----------------------|---------------|--------|------|------|------|--------------------------------------------------------------------------------------|
|                       |               | Min.   | Typ. | Max. |      |                                                                                      |
| Gate to source charge | $Q_{gs}$      | -      | 12   | -    | nC   | $V_{DD}=480\text{ V}$ ,<br>$I_D=14.5\text{ A}$ ,<br>$V_{GS}=0\text{ to }10\text{ V}$ |
| Gate to drain charge  | $Q_{gd}$      | -      | 49   | -    |      |                                                                                      |
| Gate charge total     | $Q_g$         | -      | 96   | -    |      |                                                                                      |
| Gate plateau voltage  | $V_{plateau}$ | -      | 5.4  | -    | V    |                                                                                      |

**Table 9 Reverse diode characteristics**

| Parameter                     | Symbol    | Values |      |      | Unit          | Note / Test Condition                                                                              |
|-------------------------------|-----------|--------|------|------|---------------|----------------------------------------------------------------------------------------------------|
|                               |           | Min.   | Typ. | Max. |               |                                                                                                    |
| Diode forward voltage         | $V_{SD}$  | -      | 0.9  | -    | V             | $V_{GS}=0\text{ V}$ , $I_F=14.5\text{ A}$ ,<br>$T_j=25\text{ °C}$                                  |
| Reverse recovery time         | $t_{rr}$  | -      | 510  | -    | ns            | $V_R=400\text{ V}$ , $I_F=14.5\text{ A}$ ,<br>$di_F/dt=100\text{ A}/\mu\text{s}$<br>(see table 22) |
| Reverse recovery charge       | $Q_{rr}$  | -      | 10   | -    | $\mu\text{C}$ |                                                                                                    |
| Peak reverse recovery current | $I_{rrm}$ | -      | 39   | -    | A             |                                                                                                    |

## 5 Electrical characteristics diagrams

Table 10

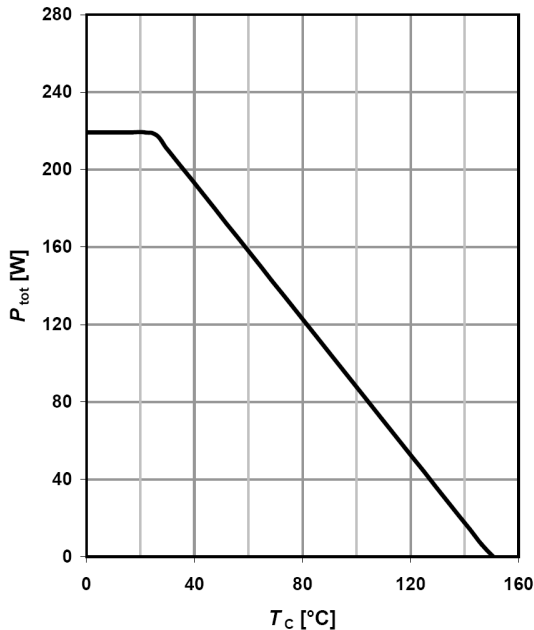
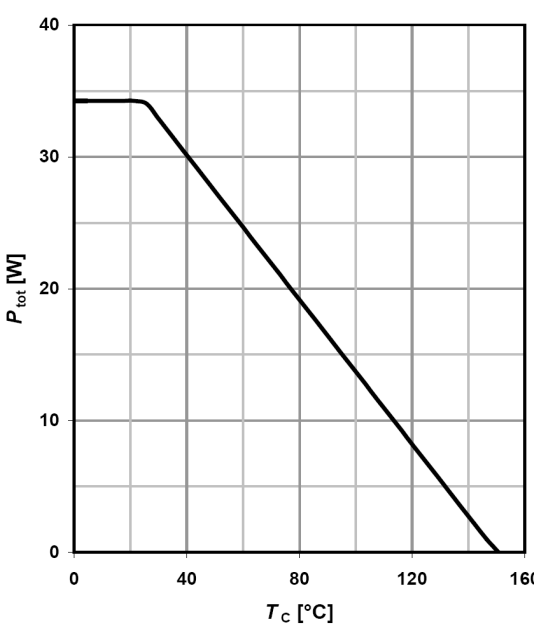
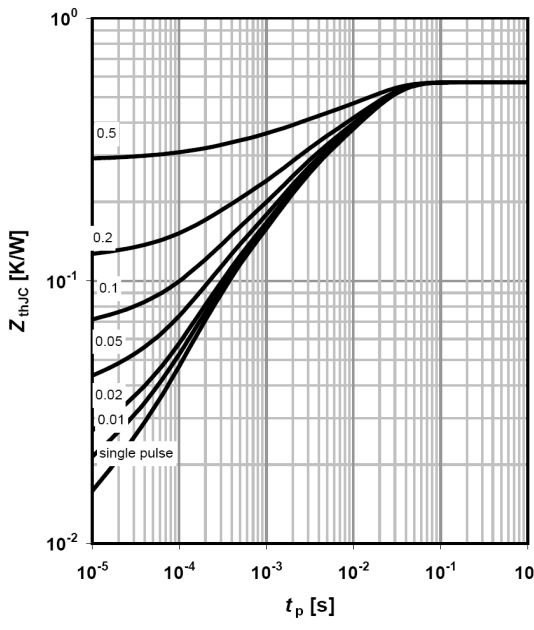
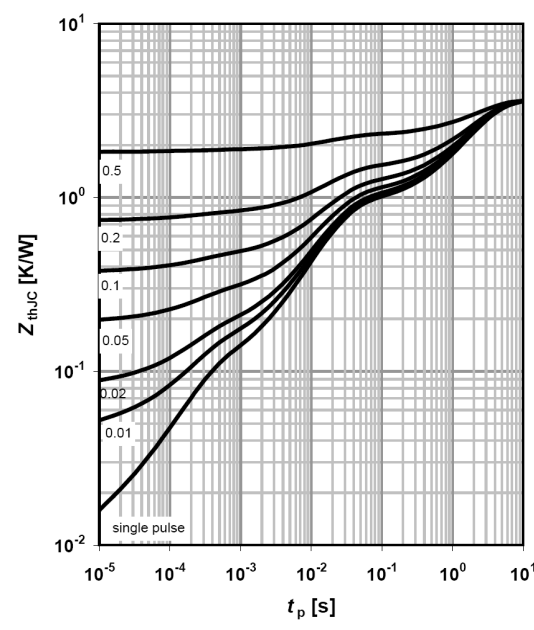
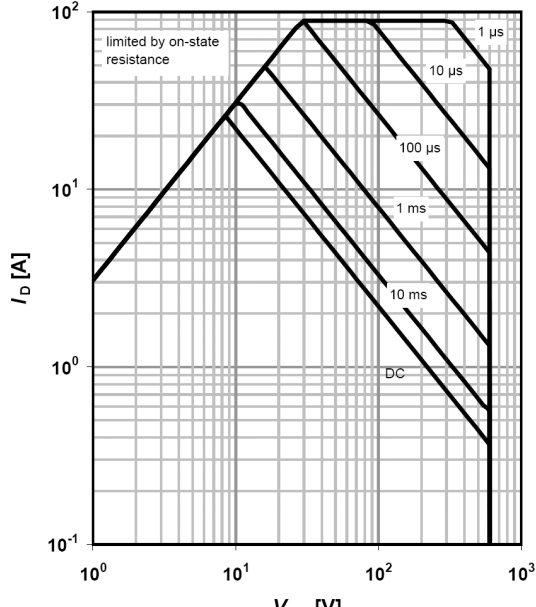
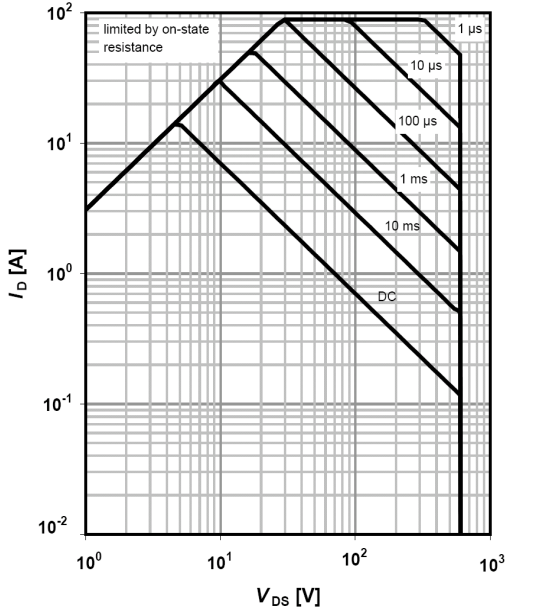
| Power dissipation<br>TO-220, TO-247, TO-263                                        | Power dissipation<br>TO-220 FullPAK                                                 |
|------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
|  |  |
| $P_{\text{tot}} = f(T_c)$                                                          | $P_{\text{tot}} = f(T_c)$                                                           |

Table 11

| Max. transient thermal impedance<br>TO-220, TO-247, TO-263                          | Max. transient thermal impedance<br>TO-220 FullPAK                                   |
|-------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------|
|  |  |
| $Z_{(\text{thJC})} = f(t_p)$ ; parameter: $D = t_p / T$                             | $Z_{(\text{thJC})} = f(t_p)$ ; parameter: $D = t_p / T$                              |

**Electrical characteristics diagrams**
**Table 12**

| Safe operating area $T_C=25\text{ °C}$<br>TO-220, TO-247, TO-263                   | Safe operating area $T_C=25\text{ °C}$<br>TO-220 FullPAK                            |
|------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
|  |  |
| $I_D=f(V_{DS}); T_C=25\text{ °C}; D=0; \text{parameter } t_p$                      | $I_D=f(V_{DS}); T_C=25\text{ °C}; D=0; \text{parameter } t_p$                       |

**Table 13**

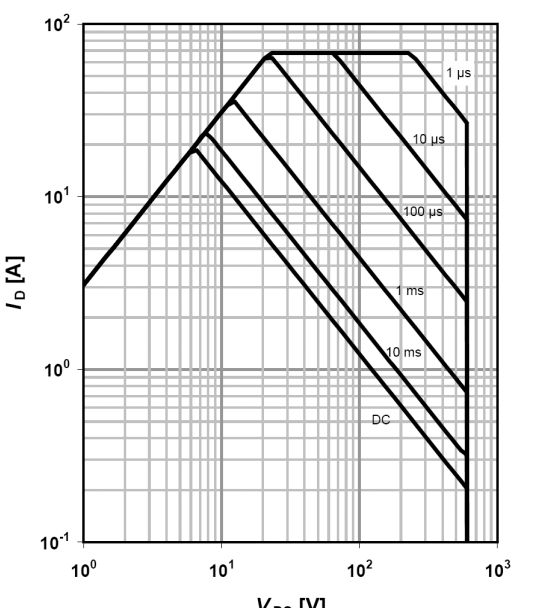
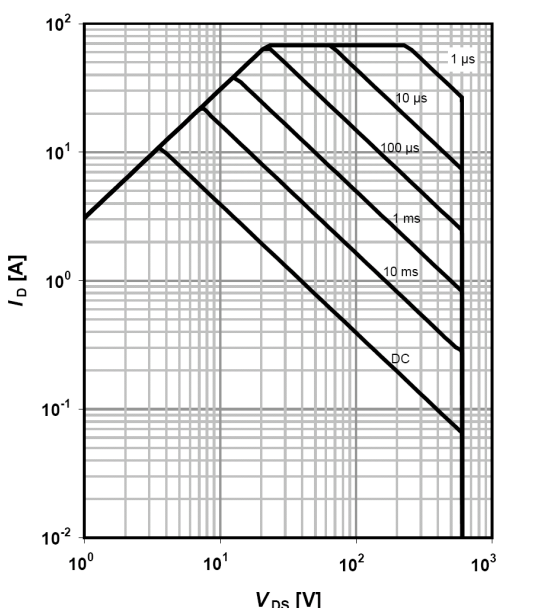
| Safe operating area $T_C=80\text{ °C}$<br>TO-220, TO-247, TO-263                    | Safe operating area $T_C=80\text{ °C}$<br>TO-220 FullPAK                             |
|-------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------|
|  |  |
| $I_D=f(V_{DS}); T_C=80\text{ °C}; D=0; \text{parameter } t_p$                       | $I_D=f(V_{DS}); T_C=80\text{ °C}; D=0; \text{parameter } t_p$                        |

Table 14

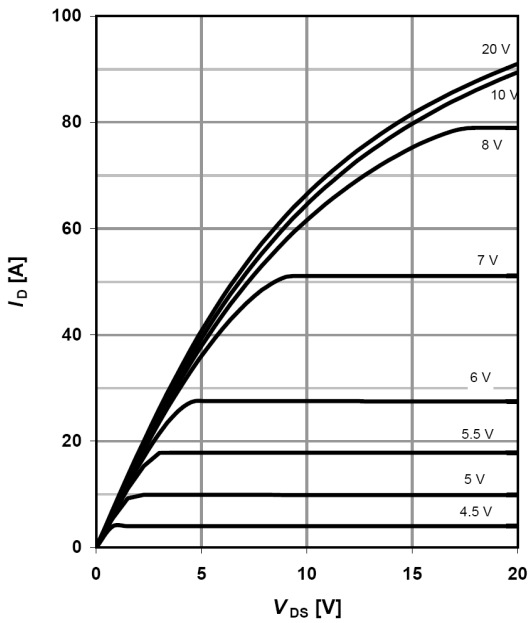
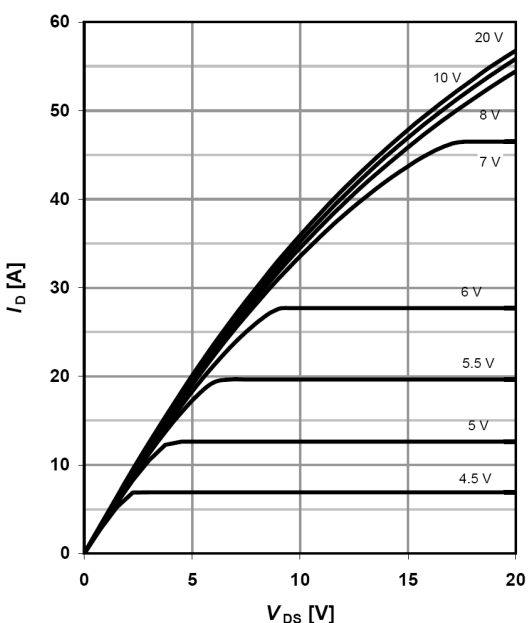
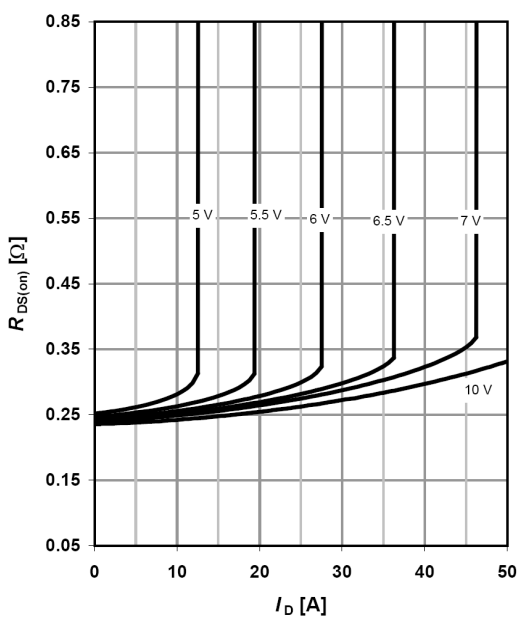
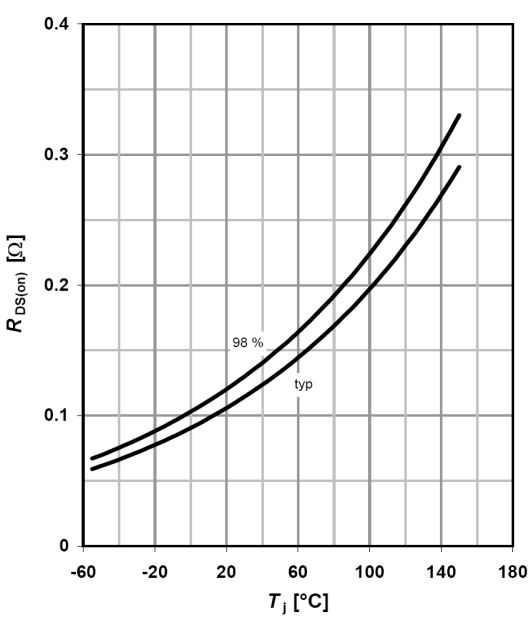
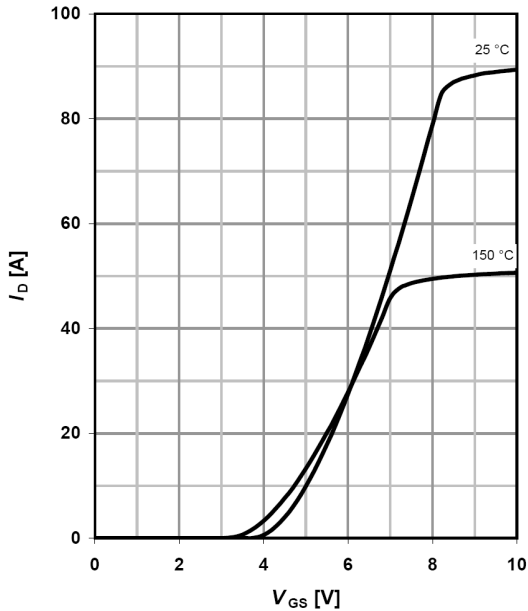
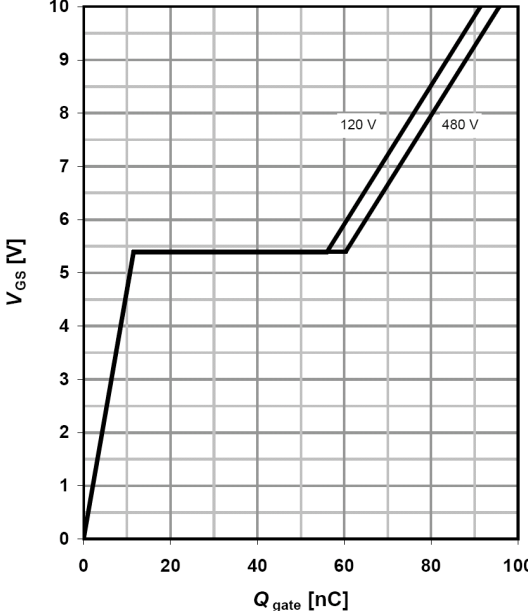
| Typ. output characteristics $T_J=25\text{ }^{\circ}\text{C}$                       | Typ. output characteristics $T_J=125\text{ }^{\circ}\text{C}$                       |
|------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
|  |  |
| $I_D=f(V_{DS}); T_J=25\text{ }^{\circ}\text{C}; \text{parameter: } V_{GS}$         | $I_D=f(V_{DS}); T_J=125\text{ }^{\circ}\text{C}; \text{parameter: } V_{GS}$         |

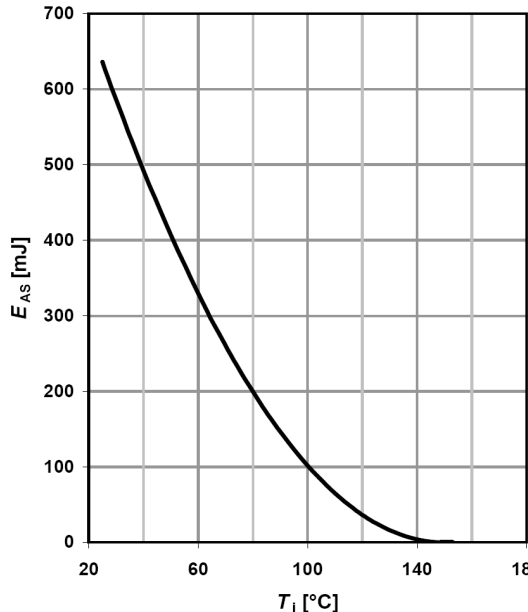
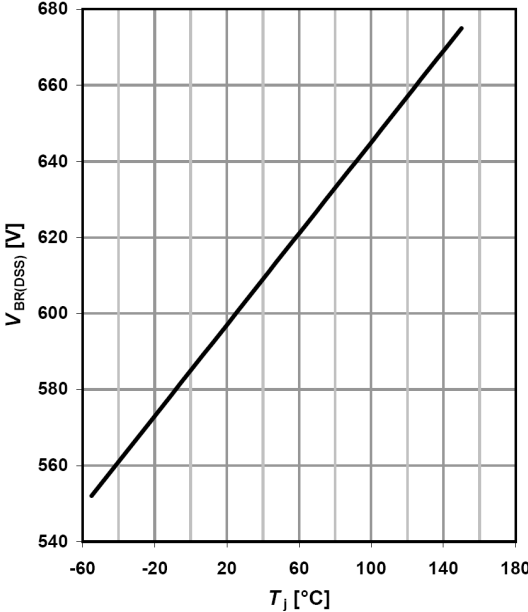
Table 15

| Typ. drain-source on-state resistance                                               | Drain-source on-state resistance                                                     |
|-------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------|
|  |  |
| $R_{DS(on)}=f(I_D); T_J=125\text{ }^{\circ}\text{C}; \text{parameter: } V_{GS}$     | $R_{DS(on)}=f(T_J); I_D=14.5\text{ A}; V_{GS}=10\text{ V}$                           |

**Table 16**

| Typ. transfer characteristics                                                      | Typ. gate charge                                                                    |
|------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
|  |  |
| $I_D = f(V_{GS}); V_{DS} = 20V$                                                    | $V_{GS} = f(Q_{gate}), I_D = 14.5 A \text{ pulsed}$                                 |

**Table 17**

| Avalanche energy                                                                    | Drain-source breakdown voltage                                                       |
|-------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------|
|  |  |
| $E_{AS} = f(T_J); I_D = 5.2 A; V_{DD} = 50 V$                                       | $V_{BR(DSS)} = f(T_J); I_D = 0.25 mA$                                                |

Electrical characteristics diagrams

Table 18

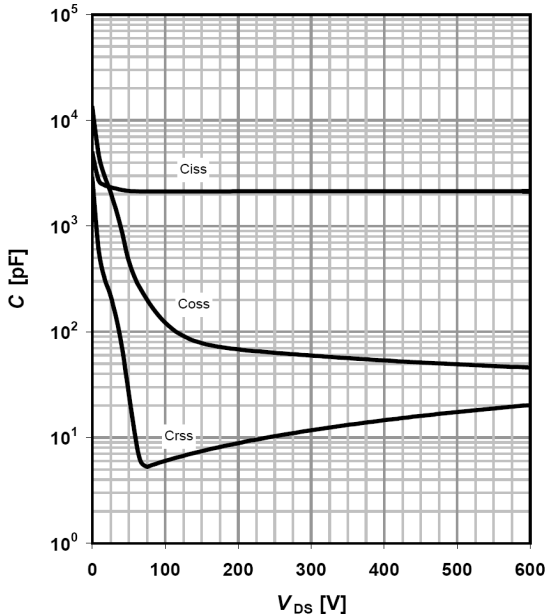
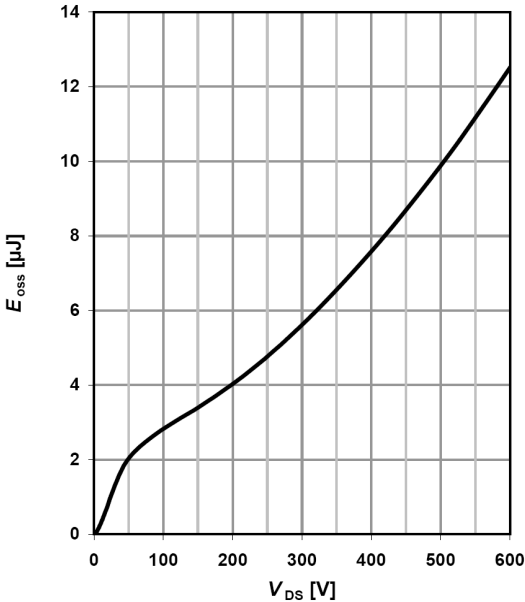
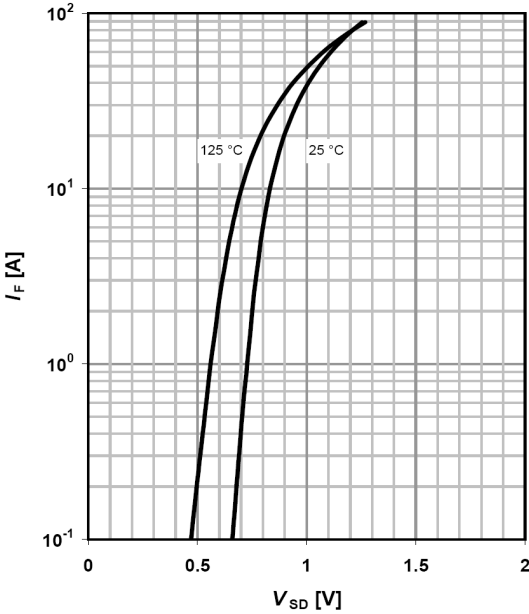
| Typ. capacitances                                                                  | Typ. $C_{oss}$ stored energy                                                        |
|------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
|  |  |
| $C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$                                   | $E_{oss}=f(V_{DS})$                                                                 |

Table 19

| Forward characteristics of reverse diode                                            |
|-------------------------------------------------------------------------------------|
|  |
| $I_F=f(V_{SD}); \text{parameter: } T_j$                                             |

## 6 Test circuits

Table 20 Switching times test circuit and waveform for inductive load

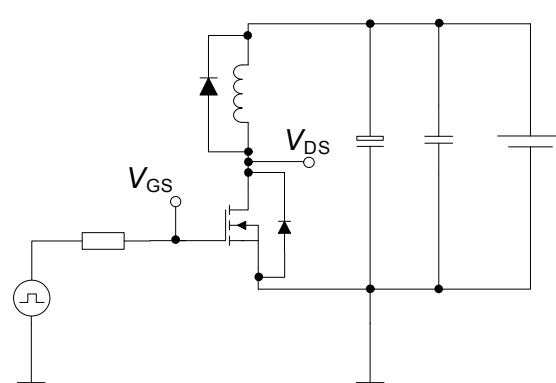
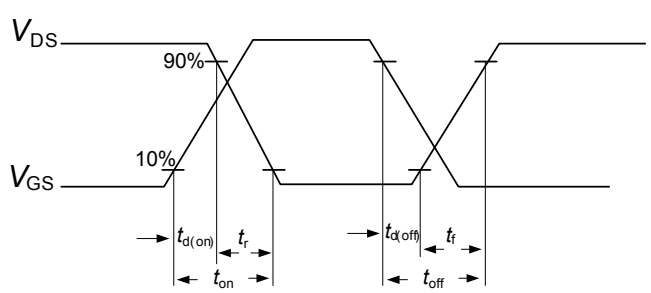
| Switching times test circuit for inductive load                                   | Switching time waveform                                                            |
|-----------------------------------------------------------------------------------|------------------------------------------------------------------------------------|
|  |  |

Table 21 Unclamped inductive load test circuit and waveform

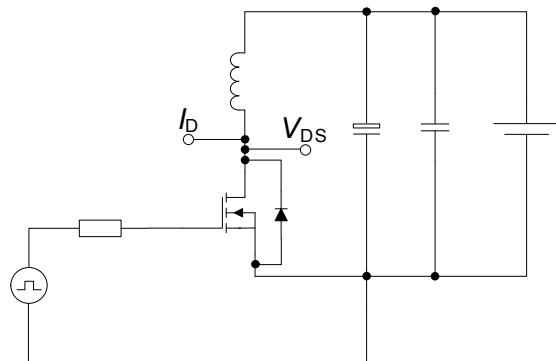
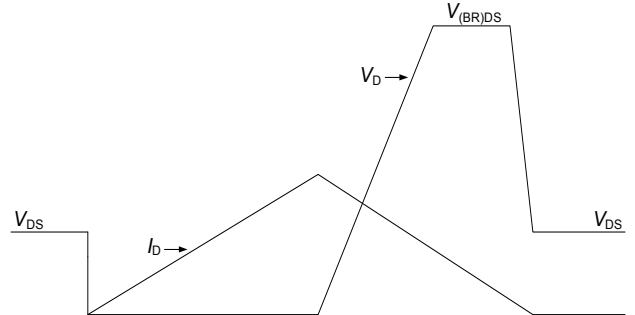
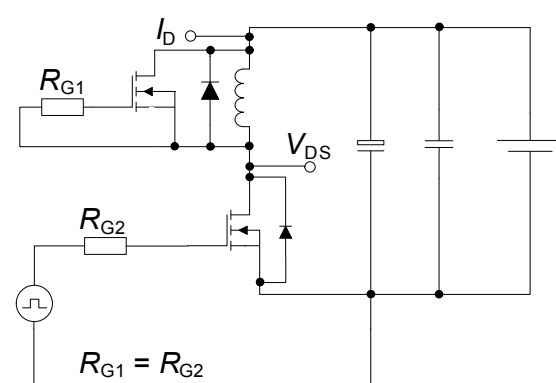
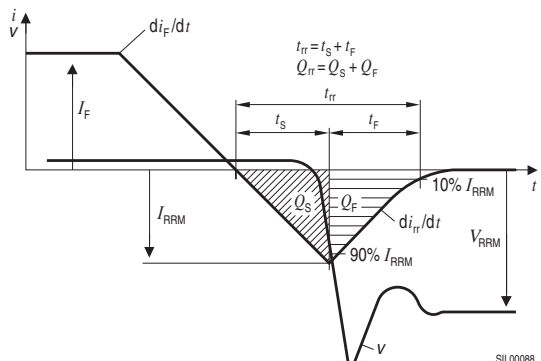
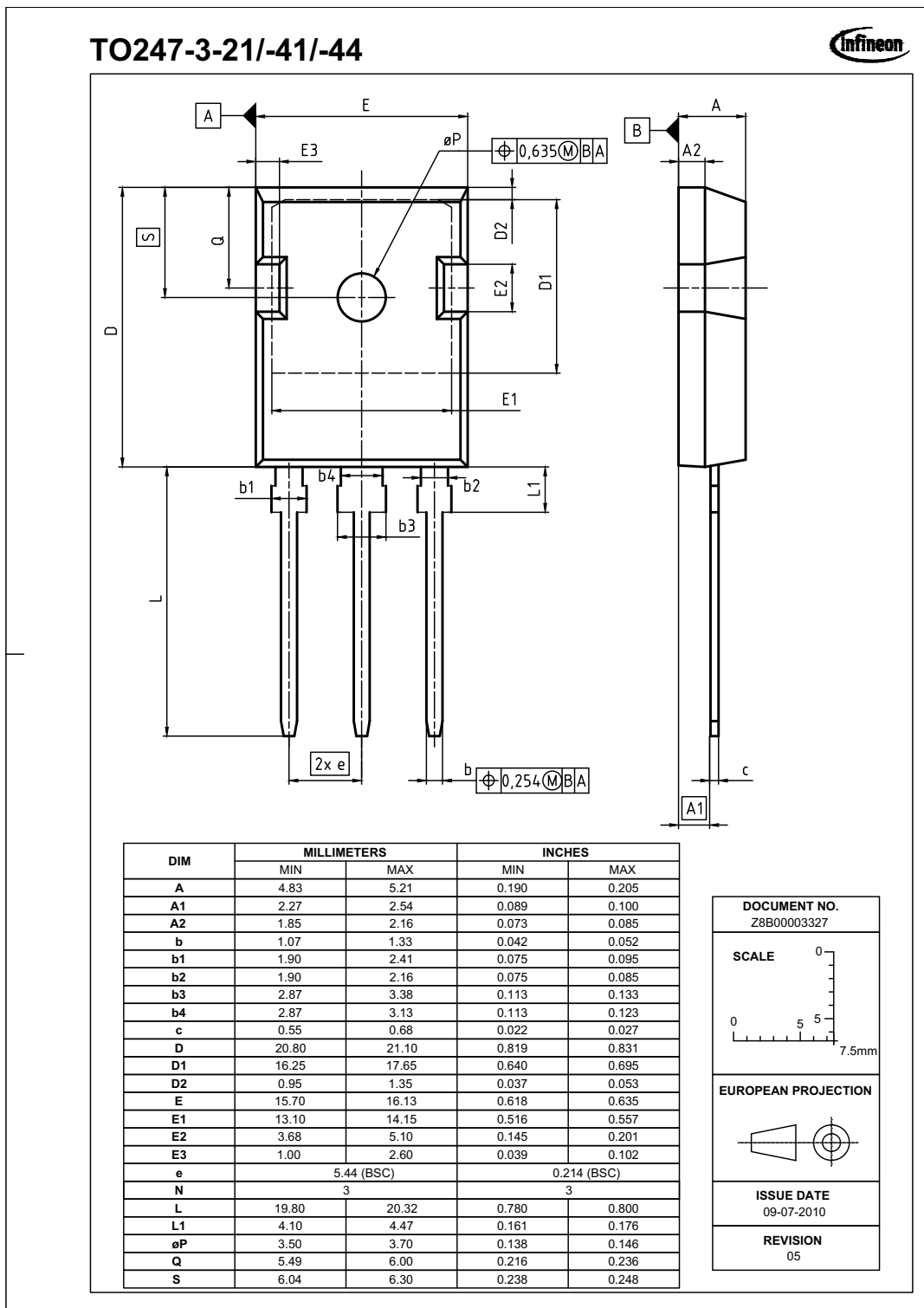
| Unclamped inductive load test circuit                                               | Unclamped inductive waveform                                                         |
|-------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------|
|  |  |

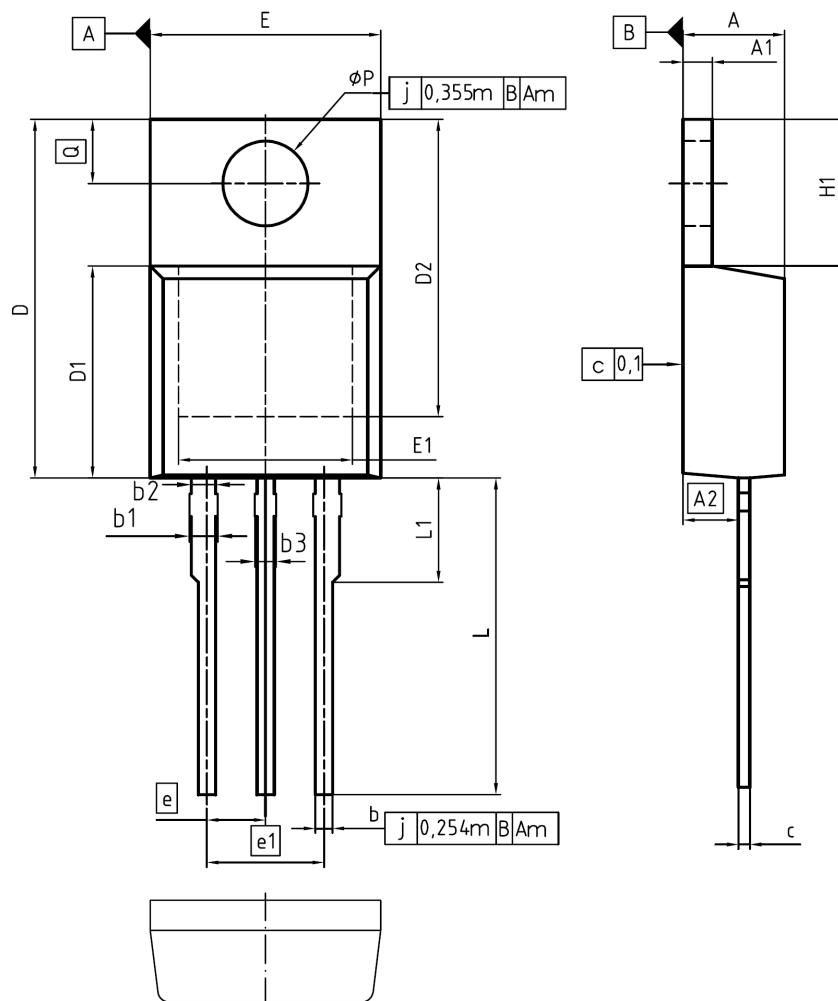
Table 22 Test circuit and waveform for diode characteristics

| Test circuit for diode characteristics                                                                                  | Diode recovery waveform                                                                                                                                                                                                                                                                  |
|-------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
|  <p><math>R_{G1} = R_{G2}</math></p> |  <p><math>t_{rr} = t_s + t_f</math><br/><math>Q_{rr} = Q_s + Q_f</math></p> <p>10% <math>I_{RRM}</math><br/>90% <math>I_{RRM}</math><br/><math>V_{RRM}</math><br/><math>V</math></p> <p>SIL00088</p> |

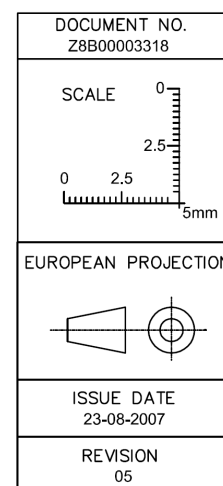
# 7 Package outlines



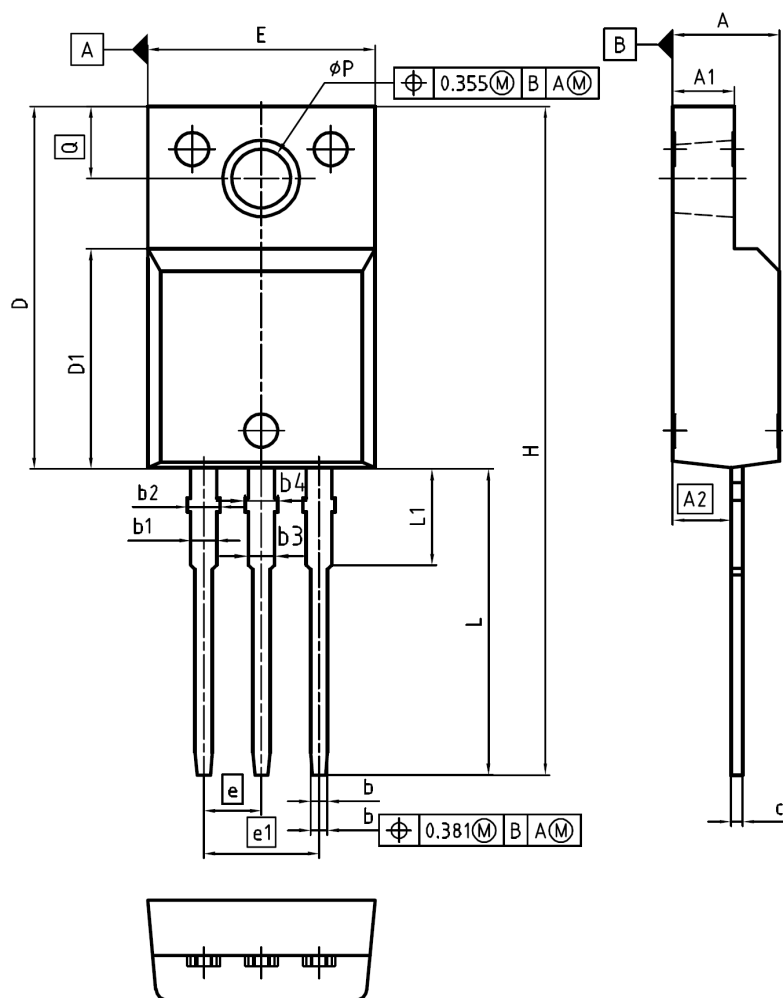
**Figure 1 Outlines TO-247, dimensions in mm/inches**



| DIM | MILLIMETERS |       | INCHES |       |
|-----|-------------|-------|--------|-------|
|     | MIN         | MAX   | MIN    | MAX   |
| A   | 4.30        | 4.57  | 0.169  | 0.180 |
| A1  | 1.17        | 1.40  | 0.046  | 0.055 |
| A2  | 2.15        | 2.72  | 0.085  | 0.107 |
| b   | 0.65        | 0.86  | 0.026  | 0.034 |
| b1  | 0.95        | 1.40  | 0.037  | 0.055 |
| b2  | 0.95        | 1.15  | 0.037  | 0.045 |
| b3  | 0.65        | 1.15  | 0.026  | 0.045 |
| c   | 0.33        | 0.60  | 0.013  | 0.024 |
| D   | 14.81       | 15.95 | 0.583  | 0.628 |
| D1  | 8.51        | 9.45  | 0.335  | 0.372 |
| D2  | 12.19       | 13.10 | 0.480  | 0.516 |
| E   | 9.70        | 10.36 | 0.382  | 0.408 |
| E1  | 6.50        | 8.60  | 0.256  | 0.339 |
| e   | 2.54        |       | 0.100  |       |
| e1  | 5.08        |       | 0.200  |       |
| N   | 3           |       | 3      |       |
| H1  | 5.90        | 6.90  | 0.232  | 0.272 |
| L   | 13.00       | 14.00 | 0.512  | 0.551 |
| L1  | -           | 4.80  | -      | 0.189 |
| øP  | 3.60        | 3.89  | 0.142  | 0.153 |
| Q   | 2.60        | 3.00  | 0.102  | 0.118 |



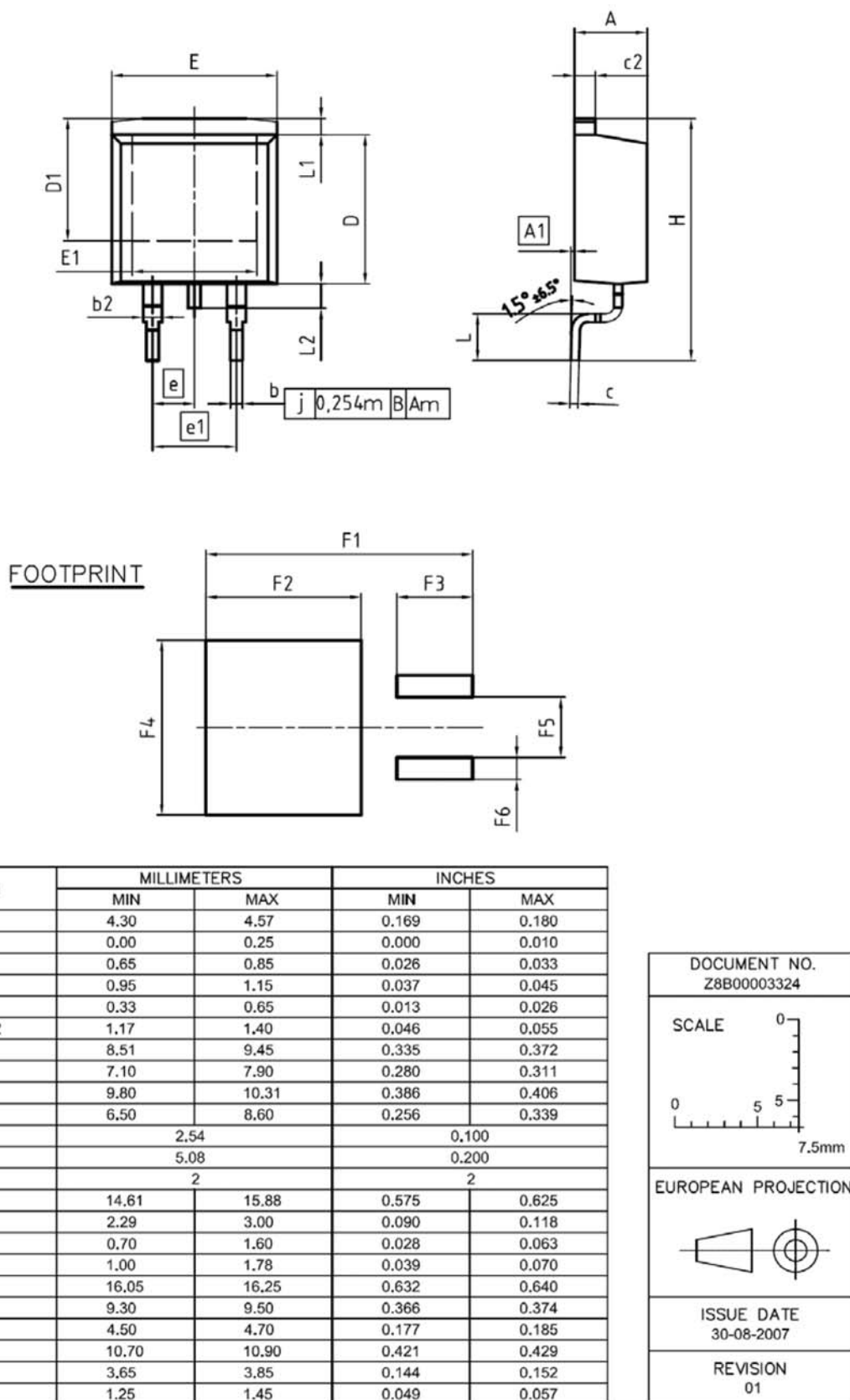
**Figure 2** Outlines TO-220, dimensions in mm/inches



| DIM | MILLIMETERS |       | INCHES |       |
|-----|-------------|-------|--------|-------|
|     | MIN         | MAX   | MIN    | MAX   |
| A   | 4.55        | 4.85  | 0.179  | 0.191 |
| A1  | 2.55        | 2.85  | 0.100  | 0.112 |
| A2  | 2.42        | 2.72  | 0.095  | 0.107 |
| b   | 0.65        | 0.85  | 0.026  | 0.033 |
| b1  | 0.95        | 1.33  | 0.037  | 0.052 |
| b2  | 0.95        | 1.51  | 0.037  | 0.059 |
| b3  | 0.65        | 1.33  | 0.026  | 0.052 |
| b4  | 0.65        | 1.51  | 0.026  | 0.059 |
| c   | 0.40        | 0.63  | 0.016  | 0.025 |
| D   | 15.85       | 16.15 | 0.624  | 0.636 |
| D1  | 9.53        | 9.83  | 0.375  | 0.387 |
| E   | 10.35       | 10.65 | 0.407  | 0.419 |
| e   | 2.54        |       | 0.100  |       |
| e1  | 5.08        |       | 0.200  |       |
| N   | 3           |       | 3      |       |
| H   | 29.45       | 29.75 | 1.159  | 1.171 |
| L   | 13.45       | 13.75 | 0.530  | 0.541 |
| L1  | 3.15        | 3.45  | 0.124  | 0.136 |
| øP  | 2.95        | 3.20  | 0.116  | 0.126 |
| Q   | 3.15        | 3.50  | 0.124  | 0.138 |

|                                                                                                              |
|--------------------------------------------------------------------------------------------------------------|
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| SCALE<br>0 2.5 5mm                                                                                           |
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| ISSUE DATE<br>08-03-2007                                                                                     |
| REVISION<br>03                                                                                               |

**Figure 3 Outlines TO-220 FullPAK, dimensions in mm/inches**



**Figure 5** Outlines TO-263, dimensions in mm/inches

## 8 Revision History

### CoolMOS C6 600V CoolMOS™ C6 Power Transistor

**Revision History: 2010-02-09, Rev. 2.1**

#### Previous Revision:

| Revision | Subjects (major changes since last revision) |
|----------|----------------------------------------------|
| 2.0      | Release of final data sheet                  |
| 2.1      | New package outlines TO-247                  |
|          |                                              |
|          |                                              |

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